XBS104V14R-G

Schottky Barrier Diode, 1A, 40V Type

■FEATURES

- Forward Voltage Forward Current Repetitive Peak Reverse Voltage Environmentally Friendly
- : V_F=0.365V (TYP.) : I_{F(AV)}=1A
- : V_{RM}=40V
- : EU RoHS Compliant, Pb Free

■ABSOLUTE MAXIMUM RATINGS

	1a=25				
PARAMETER	SYMBOL	RATINGS	UNIT		
Repetitive Peak Reverse Voltage	Vrm	40	V		
Reverse Voltage (DC)	Vr	40	V		
Forward Current (Average)	IF(AV)	1	А		
Non Continuous	IFSM	20	А		
Forward Surge Current ^{*1}	IFSM	20			
Junction Temperature	Tj	125	°C		
Storage Temperature Range	Tstg	-55~+150	°C		

*1 : Non continuous high amplitude 60Hz half-sine wave.

* When the IC is operated continuously under high load conditions such as high temperature, high current and high voltage, it may have the case that reliability reduces drastically even if under the absolute maximum ratings. Adequate "Derating" should be taken into consideration while designing.

■MARKING RULE

①: 0 (Product Number)
 ②: Assembly Lot Number

PRODUCT NAME

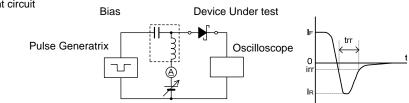
PRODUCT NAME	DEVICE ORIENTATION
XBS104V14R-G	SOD-123A(Halogen & Antimony free)
XBS104V14R	SOD-123A

* The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

* The device orientation is fixed in its embossed tape pocket.

ELECTRICAL CHARACTERISTICS

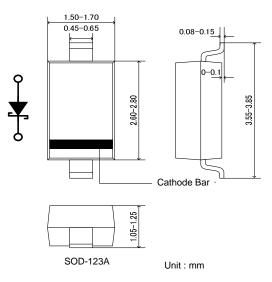
PARAMETER SYME	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
	STNIBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Forward Voltage	VF1	I _F =100mA	-	0.23	0.315	V
	VF2	I _F =500mA	-	0.30	0.385	V
	VF3	I _F =1A	-	0.365	0.41	V
Reverse Current	IR	V _R =40V	-	0.25	2	mA
Inter-Terminal Capacity	Ct	V _R =1V , f=1MHz	-	150	-	pF
Reverse Recovery Time ^{*2}	trr	I _F =I _R =10mA , irr=1mA	-	41	-	ns
*2 : trr measurement circuit				•		



■ APPLICATIONS

- Rectification
- Protection against reverse connection of battery

■PACKAGING INFORMATION



1a=25 C

1/3

Ta=25°C

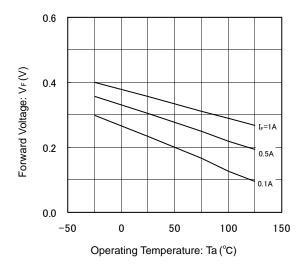
ETR1610-002

■TYPICAL PERFORMANCE CHARACTERISTICS

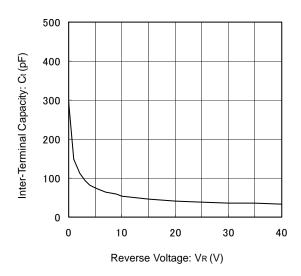
(1) Forward Current vs. Forward Voltage

(P) 0.1 0.01 0.01 0.01 0.02 0.4 0.6 Forward Voltage: VF (V)

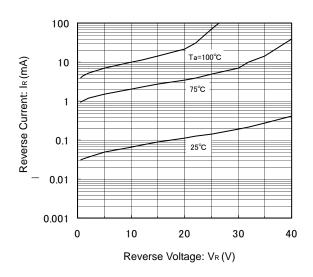
(3) Forward Voltage vs. Operating Temperature



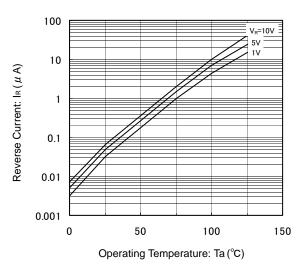
(5) Inter-Terminal Capacity vs. Reverse Voltage



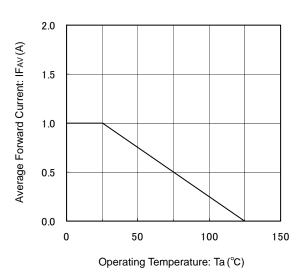
(2) Reverse Current vs. Reverse Voltage



(4) Reverse Current vs. Operating Temperature



(6) Average Forward Current vs. Operating Temperature



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